

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	68	((multilayer or multilevel or plurality or multiple) near10 (conducting or conductive) near10 film) same ((scan or scanning) adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:16
L3	44	((multilayer or multilevel or plurality or multiple) near10 (conducting or conductive) near10 film) same ((scan or scanning) adj line) same (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:17
L5	1	((multilayer or multilevel or plurality or multiple) near10 (conducting or conductive) near10 film) same ((scan or scanning) adj line) same (tft or (thin adj film adj transistor)) and (nitrogen near concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:19
L4	10	((multilayer or multilevel or plurality or multiple) near10 (conducting or conductive) near10 film) same ((scan or scanning) adj line) same (tft or (thin adj film adj transistor)) and nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:18
L15	85	((nitrogen adj concentration) with (tin or (titanium adj nitride)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:28
L14	39	((nitrogen adj concentration) with (tin or (titanium adj nitride))) and ((tin or (titanium adj nitride)) with (al or aluminum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:28
L1	7867	(multilayer or multilevel or plurality or multiple) near10 (conducting or conductive) near10 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:16
L13	288	(nitrogen adj concentration) and ((tin or (titanium adj nitride)) with (al or aluminum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:27
L12	14	(nitrogen adj concentration) with (tin or (titanium adj nitride)) with (al or aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:27

L9	689	(nitrogen adj concentration).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:25
L10	30	(nitrogen adj concentration).clm. and (tin or (titanium adj nitride)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:25
L11	4	(nitrogen adj concentration).clm. and (tin or (titanium adj nitride)). clm. with (al or aluminum).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:26
L18	9	(tin or (titanium adj nitride)) and (nitrogen adj concentration) and ((gate adj electrode) near10 ((scan or scanning) adj line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:32
L19	5	(tin or (titanium adj nitride)) and (nitrogen adj concentration) and ((gate adj electrode) near10 ((scan or scanning) adj line)) and ((active adj matrix adj substrate) near5 plate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:34
L20	5	(tin or (titanium adj nitride)) and (nitrogen adj concentration) and ((gate adj electrode) near10 ((scan or scanning) adj line)) and ((active adj matrix adj substrate) near5 plate) and ((tft or (thin adj film adj transistor)) near10 plate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:42
L17	9	(tin or (titanium adj nitride)) and (nitrogen adj concentration) and ((gate adj electrode) with ((scan or scanning) adj line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:32
L16	47	(tin or (titanium adj nitride)) and (nitrogen adj concentration) and (gate adj electrode) and ((scan or scanning) adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:31
L6	6	(tin or (titanium adj nitride)) same ((scan or scanning) adj line) same (tft or (thin adj film adj transistor)) and (nitrogen near concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:23

L7	3	(tin or (titanium adj nitride)) same (al or aluminum) same ((scan or scanning) adj line) same (tft or (thin adj film adj transistor)) and (nitrogen near concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:25
L8	2	(tin or (titanium adj nitride)) same (al or aluminum) same ((scan or scanning) adj line) same (tft or (thin adj film adj transistor)) same (nitrogen near concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/21 12:24